

Amended Claims

1. (withdrawn) A LVTSCR-like structure having one or more diodes formed in a p-well of the structure.
2. (currently amended) A method of increasing the holding voltage of an LVTSCR structure that includes an n-well and a p-well formed in a substrate, a gate, a first n+ region and a first p+ region formed in the n-well to define a high voltage node on one side of the gate, and a second n+ region and a second p+ region formed in the p-well to define a low voltage node on the other side of the gate, the method comprising forming an additional n+ region inside the p-well of the structure to define a diode with a p-n junction between a p-type material as defined by the additional n+ region and the p-well and, with the second p+ region forming a contact to in the diode p-well, and an n-type material as defined by the additional n+ region, the p-n junction being forward biased during normal operation by having said additional n+ region of the p-n junction located further from the high voltage node than the second p+ region.
3. (previously presented) A method of increasing the holding voltage of an LVTSCR structure having an anode in an n-well and a cathode in a p-well, the cathode being defined by an n+ region and a p+ region, comprising forming at least one additional n+ region and at least one additional p+ region in the p-well to define at least one forward biased diode under normal operation in the p-well, thereby providing an alternative current path from anode to cathode through said at least one diode.
4. (original) A method of claim 3, wherein the alternative current path defines a lower resistance current path than the p-well.
5. (canceled)
6. (canceled)
7. (canceled)

8. (canceled)
9. (currently amended) A method of claim 2, further comprising forming at least one additional p+ region and multiple additional n+ regions inside the p-well of the structure to define multiple diodes each with a p-n junction junctions in the p-well, each diode p-n junction being formed between a p-type material and an n-type material, wherein the p-type material is defined by the p-well and having one of the additional p+ regions or the second p+ region as diode contact, and wherein the n-type material is as defined by one of the additional n+ regions.